Ť	N7	II i to	Search Text	DB	Time stamp
	Number	Hits 3	"18249"	EPO; JPO;	2003/11/18 14:56
,1		3	16249"	DERWENT	2000,11,10 11.00
2		669	miyakawa.in.	EPO; JPO; DERWENT	2003/11/18 14:56
3		10	miyakawa.in. and plasma	EPO; JPO; DERWENT	2003/11/18 15:01
4		26	barnes-michael.in. cox-michael-s\$.in.	EPO; JPO; DERWENT	2003/11/18 15:02
5		58	lai-canfeng.in. parks-joun.in. barnes-michael.in. cox-michael-s\$.in.	USPAT; US-PGPUB	2003/11/18 15:02
-		0	lai-canfeng.in. parks-joun.in. (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) with silylation with	USPAT; US-PGPUB	2003/05/13 11:25
-		0	cur\$3) (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) same silylation same	USPAT; US-PGPUB	2003/05/13 11:32
-		1	cur\$3) 09/502,126	USPAT; US-PGPUB	2003/05/13 11:23
-		3534	atmospher\$3 with pressure with plasma	USPAT; US-PGPUB	2003/05/13 11:26
-		1709	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.	USPAT; US-PGPUB	2003/05/13 12:34
-		50	(atmospher\$3 with pressure with plasma) and ((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 11:26
-		6 3	5578130.URPN. (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) same silicon same	USPAT; USPAT; US-PGPUB	2003/05/13 11:30 2003/05/13 11:34
-		49	cur\$3) (cur\$3 with chamber) and (anneal\$3 with chamber) and ((silicon silylation) with	USPAT; US-PGPUB	2003/05/13 12:17
-		8	chamber) ("4944895"   "5047369"   "5858457"   "5958577"   "6048804"   "6153511"   "6218302"   "6284682").PN.	USPAT	2003/05/13 11:57
-		1	"high pressure deposition module"	USPAT; US-PGPUB	2003/05/13 12:33
-		1374	"APCVD"	USPAT; US-PGPUB	2003/05/13 12:39
-		17	"APCVD" and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:34
-		464	"APCVD" with plasma	USPAT; US-PGPUB	2003/05/13 12:42
-		1	("APCVD" with plasma) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:39
-		9	"silylation chamber"	USPAT; US-PGPUB	2003/05/13 12:44
-		4.4	silylation with chamber	USPAT; US-PGPUB	2003/05/13 12:44
-		35	(silylation with chamber) not "silylation chamber"	USPAT; US-PGPUB	2003/05/13 13:05
-		1	("6451118").PN.	USPAT; US-PGPUB	2003/05/13 13:05
-		1667	spin with coating with uniform\$3	USPAT; US-PGPUB	2003/05/13 15:34
-		5	(spin with coating with uniform\$3) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 15:37
-		0		USPAT; US-PGPUB	2003/05/13 15:35
-		0	spin with coating with uniform\$3 same ( atmoshperic with deposit\$3)	USPAT; US-PGPUB	2003/05/13 15:36
-		162	(spin with coating with uniform\$3) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40
-		4	(spin with coating with uniform\$3 with atmospheric) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40

	3584	plasma with (atmospheric high) with	EPO; JPO;	2003/11/18 11:15
	!	pressure	DERWENT EPO; JPO;	2003/11/18 11:29
<b> •</b> -	1257	plasma with (atmospheric high) with	DERWENT	2003/11/18 11.29
		pressure with (coat\$3 deposit\$3 layer	DERWENT	
		film)	EPO; JPO;	2003/11/18 11:30
-	380	(plasma with (atmospheric high) with	DERWENT	2003/11/18 11.50
		pressure with (coat\$3 deposit\$3 layer	DEKMENT	
		film)) and c23c016\$.ipc.	EPO; JPO;	2003/11/18 12:17
-	135	(plasma with (atmospheric) with pressure	DERWENT	2003/11/10 12:1/
	İ	with (coat\$3 deposit\$3 layer film)) and	DERWENT	
	20	c23c016\$.ipc. (plasma with (atmospheric) with pressure	EPO; JPO;	2003/11/18 11:20
-	30	with (coat\$3 deposit\$3 layer film) with	DERWENT	2000, 12, 10
		(semiconductor dielectric)) and	DELVIDIVE	
		c23c016\$.ipc.		
_	3232	plasma with (atmospheric high) with	USPAT;	2003/11/18 11:29
_	3232	pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
		film)		
	20		EPO; JPO;	2003/11/18 12:59
		pressure with (coat\$3 deposit\$3 layer	DERWENT	i l
		film)) and 118/\$.ccls.		]
l _	330	(plasma with (atmospheric high) with	USPAT;	2003/11/18 12:59
		pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
	1	film)) and 118/\$.ccls.		
-	2	(plasma with (atmospheric high) with	USPAT;	2003/11/18 11:31
		pressure with (coat\$3 deposit\$3 layer	US-PGPUB	į i
	1	film)) and 414/\$.ccls.		0000/44/20 44 31
-	135	(plasma with (atmospheric high) with	USPAT;	2003/11/18 11:31
		pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
		film)) and 156/345.\$.ccls.	menam.	2003/11/18 11:31
-	41		USPAT; US-PGPUB	2003/11/18 11.31
		pressure with (coat\$3 deposit\$3 layer film)) and 118/719.ccls.	03-FGF0B	
		("5319247").PN.	USPAT;	2003/11/18 11:53
-	1	("551924/").FN.	US-PGPUB	2000/11/10 11/00
ļ	33	5319247.URPN.	USPAT	2003/11/18 11:45
	1154		USPAT;	2003/11/18 11:54
	1101	(deposit\$3 coat\$3 film layer)	US-PGPUB	
_	376		EPO; JPO;	2003/11/18 11:54
		(deposit\$3 coat\$3 film layer)	DERWENT	
1 -	34	("atmospheric pressure" with plasma with	EPO; JPO;	2003/11/18 11:54
		(deposit\$3 coat\$3 film layer)) same	DERWENT	
		semiconductor		
-	215		USPAT;	2003/11/18 11:59
		(deposit\$3 coat\$3 film layer)) same	US-PGPUB	
		semiconductor		
-	330		USPAT;	2003/11/18 12:17
		pressure with (coat\$3 deposit\$3 layer	US-PGPUB	
		film)) and 118/\$.ccls.		2002/11/10 12-18
-	2	(in\$1line same cluster) and c23c016\$.ipc.	EPO; JPO;	2003/11/18 12:18
			DERWENT	2003/11/18 12:18
] -	9	(in\$11ine same cluster) and 118/719.ccls.	USPAT; US-PGPUB	2003/11/10 12:10
		(-1	USPAT;	2003/11/18 13:53
-	24	(plasma with "atmospheric pressure") and 118/719.ccls.	US-PGPUB	2000/11/10 10.00
	18		USPAT	2003/11/18 13:07
	18	("6342275").PN.	USPAT;	2003/11/18 14:56
-	1	( 0012210 ).114.	US-PGPUB	
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